N-Channel Enhancement Mode Field Effect Transistor

Product Summary

V_{DS}	60V
I_D	200A
$R_{DS(ON)}$(at V_{GS}=10V)	2.9 mohm
$R_{DS(ON)}$(at V_{GS}=4.5V)	3.6 mohm

100% EAS Tested

100% V_{DS} Tested

General Description

Split Gate Trench MOSFET technology

Excellent package for heat dissipation

High density cell(c)-8(e)--3(Des)4(c)-3(ription)]TJETgyUS(o)*nBTr>BDlen

Electrical Characteristics (T_J=25 unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max	Units

Typical Performance Characteristics

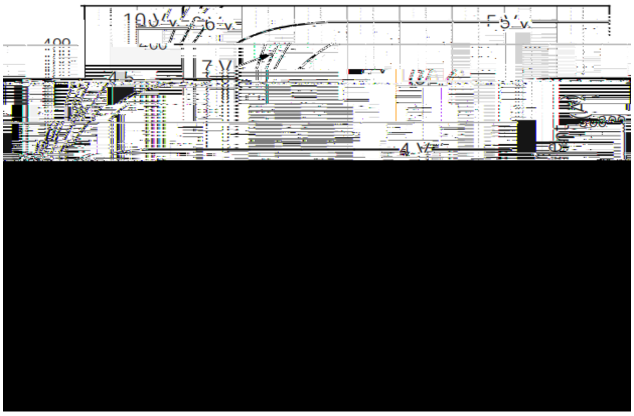


Figure1. Output Characteristics

Figure2. Transfer Characteristics

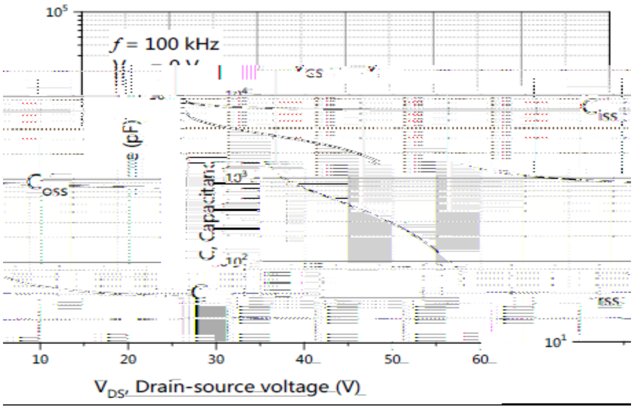


Figure3. Capacitance Characteristics

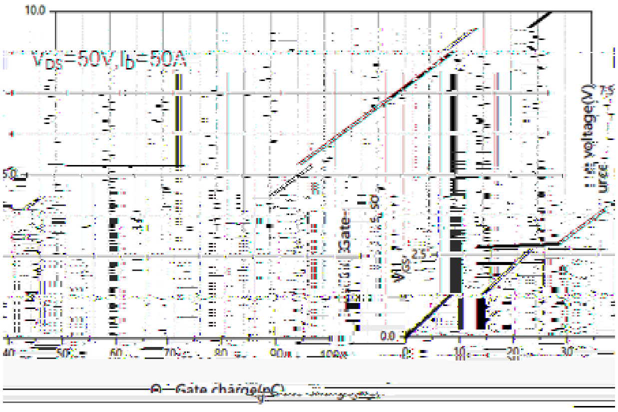


Figure4. Gate Charge

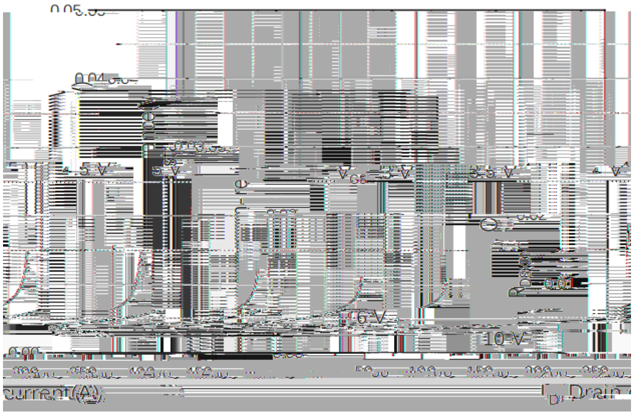


Figure5. Drain-Source on Resistance

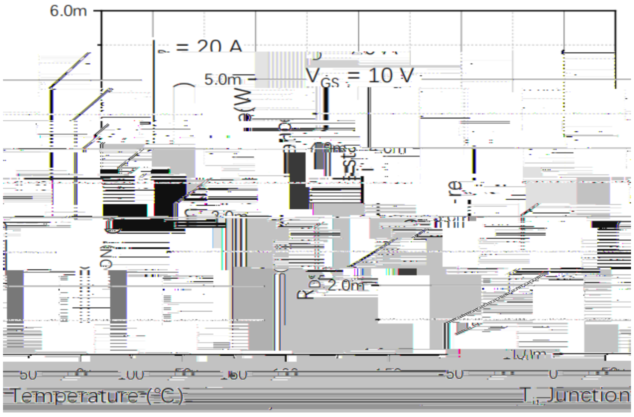


Figure6. Drain-Source on Resistance

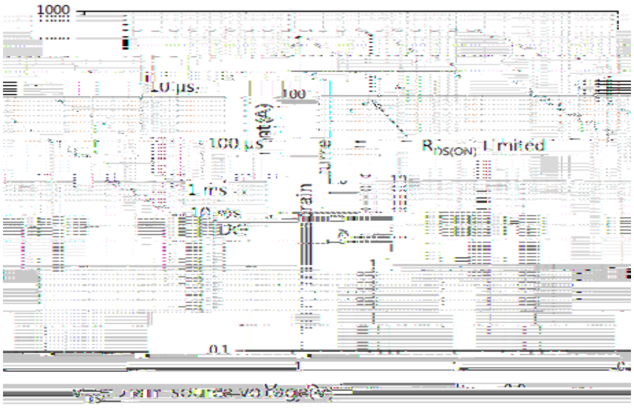


Figure7. Safe Operation Area

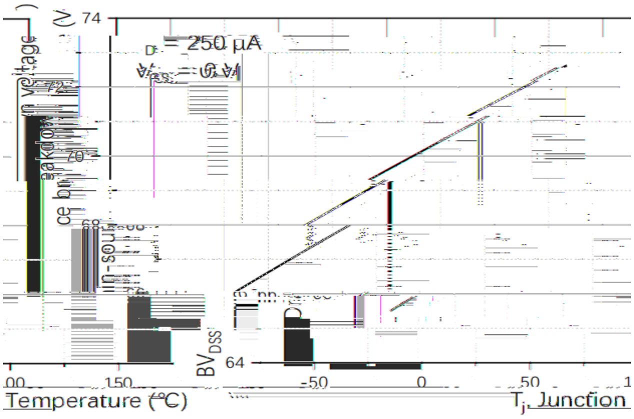


Figure8. Drain-source breakdown voltage

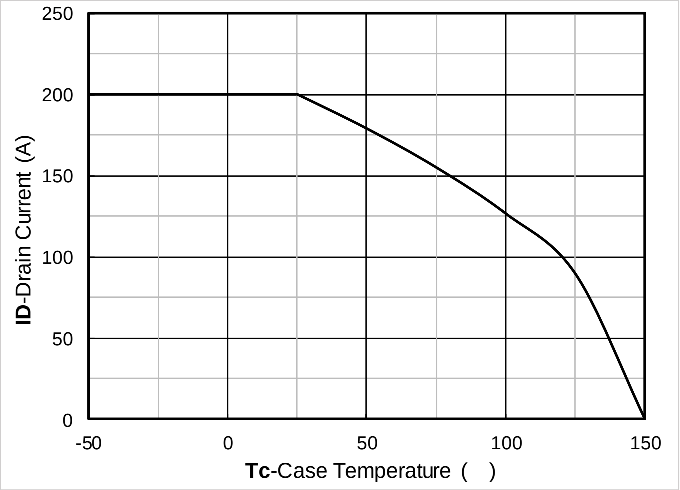
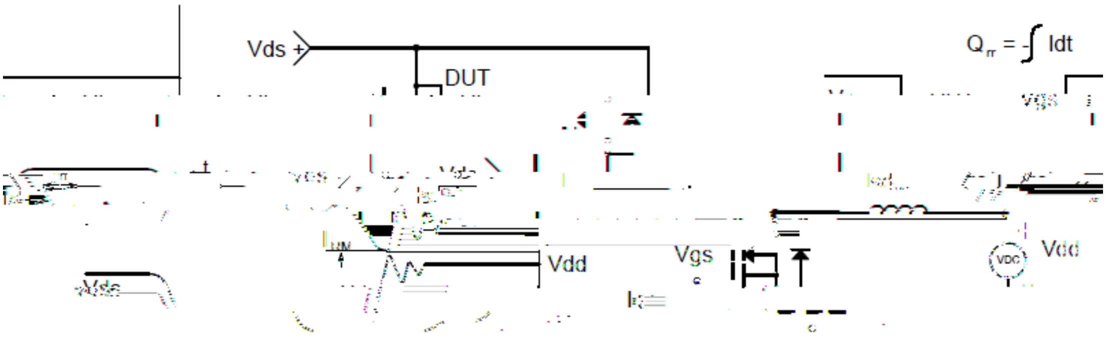


Figure 9. Current dissipation

Figure D: Diode Recovery Test Circuit & Waveforms



TO-220AB-C Package Information

NOTE:
1.PACKAGE BODY SIZES EXCLUDE MOLD FLASH AND GATE BURRS.
2.TOLERANCE 0.1mm UNLESS OTHERWISE SPECIFIED.